



Product Summary

BV _{DSS}	Max R _{DS(ON)}	Max I _D T _A = +25°C
-100V	1.0Ω @ V _{GS} = -10V	-0.7A
	1.45Ω @ V _{GS} = -6.0V	-0.5A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

100V P-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Fast Switching Speed
- Low Input Capacitance
- Low Gate Charge
- Low Threshold
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

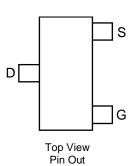
Mechanical Data

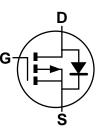
- Case: SOT23 (Type DN)
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Weight: 0.009 grams (Approximate)



SOT23 (Type DN)

Top View





Equivalent Circuit

Ordering Information (Note 5)

Part Number	Case	Packaging
ZXMP10A13FQTA	SOT23 (Type DN)	3000/Tape & Reel
ZXMP10A13FQTC	SOT23 (Type DN)	10,000/Tape & Reel

Notes: 1. No p

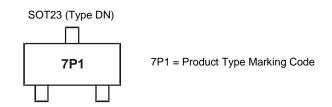
No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/product-compliance-definitions/.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit	
Drain-Source Voltage			V _{DSS}	-100	V	
Gate-Source Voltage			V _{GS}	±20	V	
Continuous Drain Current	V _{GS} = -10V	T _A = +70°C	(Note 7) (Note 7) (Note 7)	ID	-0.7 -0.5 -0.6	A
Pulsed Drain Current (Note 8)			I _{DM}	-3.1	A	
Continuous Source Current (Body Diode) (Note 6)			Is	-1.1	A	
Pulsed Source Current (Body Diode) (Note 8)			I _{SM}	-3.1	A	

Thermal Characteristics

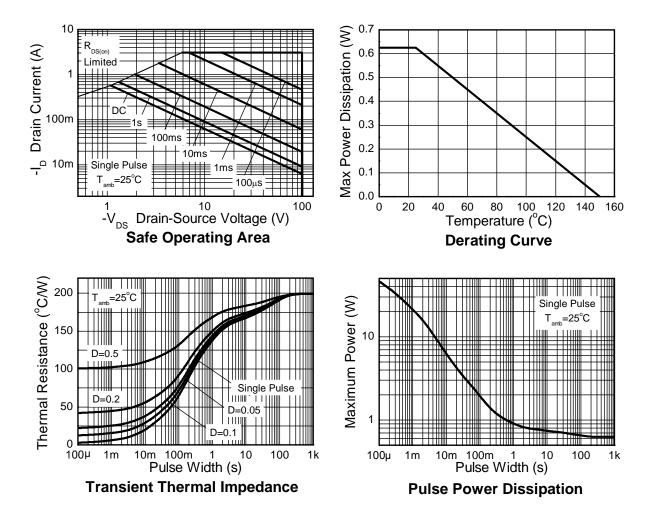
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6) Linear Derating Factor	PD	625 5	mW mW/°C
Power Dissipation (Note 7) Linear Derating Factor	PD	806 6.4	mW mW/°C
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	200	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	R _{0JA}	155	°C/W
Thermal Resistance, Junction to Leads (Note 9)	R _{θJL}	194	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

6. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.
7. For a device surface mounted on FR-4 PCB measured at t ≤ 5 secs.
8. Repetitive rating 25mm x 25mm FR-4 PCB, D = 0.05 pulse width = 10µs - pulse current limited by maximum junction temperature.
9. Thermal resistance from junction to solder-point (at the end of the drain lead).



Thermal Characteristics





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

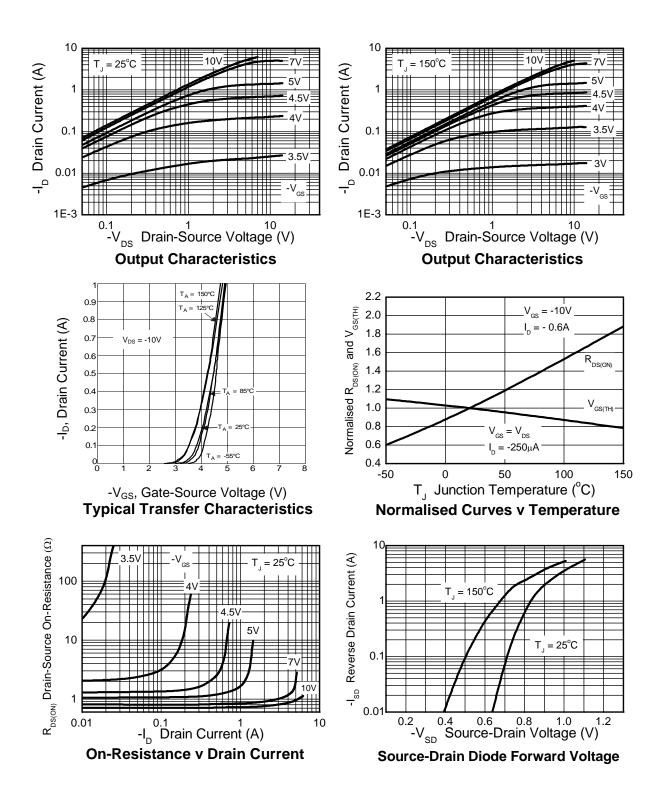
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS			•			·	
Drain-Source Breakdown Voltage	BV _{DSS}	-100		—	V	$I_D = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}		_	-1.0	μA	$V_{DS} = -100V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS						-	
Gate Threshold Voltage	V _{GS(TH)}	-2.0	_	-4.0	V	I_D = -250µA, V_{DS} = V_{GS}	
Statia Drain Source On Desistance (Note 10)	D		_	1.0	Ω	$V_{GS} = -10V, I_D = -0.6A$	
Static Drain-Source On-Resistance (Note 10)	R _{DS(ON)}	—		1.45	Ω	$V_{GS} = -6.0V, I_D = -0.5A$	
Forward Transconductance (Notes 10 and 12)	g fs	_	1.2	_	S	V _{DS} = -15V, I _D = -0.6A	
Diode Forward Voltage (Note 10)	V _{SD}	_	-0.85	-0.95	V	$T_J = +25^{\circ}C, I_S = -0.75A, V_{GS} = 0V$	
Reverse Recovery Time (Note 12)	t _{RR}		29	_	ns	T _J = +25°C, I _F = -0.9A, di/dt = 100A/µs	
Reverse Recovery Charge (Note 12)	Q _{RR}	_	31	_	nC		
DYNAMIC CHARACTERISTICS (Note 12)			•			·	
Input Capacitance	Ciss	_	141	_		$V_{DS} = -50V, V_{GS} = 0V$ f = 1.0MHz	
Output Capacitance	Coss	_	13.1	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	10.8	_			
Turn-On Delay Time (Note 11)	t _{D(ON)}	_	1.6	_		V_{DD} = -50V, I_D = -1.0A, $R_G \approx 6.0\Omega$, V_{GS} = -10V	
Turn-On Rise Time (Note 11)	t _R		2.1	_			
Turn-Off Delay Time (Note 11)	t _{D(OFF)}		5.9	_	ns		
Turn-Off Fall Time (Note 11)	t _F		3.3	_			
Total Gate Charge (Note 11)	Qg	_	1.8		nC	$V_{DS} = -50V, V_{GS} = -5.0V,$ $I_{D} = -0.6A$	
Total Gate Charge (Note 11)	Qg		3.5			$V_{DS} = -50V, V_{GS} = -10V,$	
Gate-Source Charge (Note 11)	Q _{gs}	_	0.6		nC		
Gate-Drain Charge (Note 11)	Q _{gd}		1.6		1	I _D = -0.6A	

Notes:

Measured under pulsed conditions. Pulse width = 300µs. Duty cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperature.
 For design aid only, not subject to production testing.

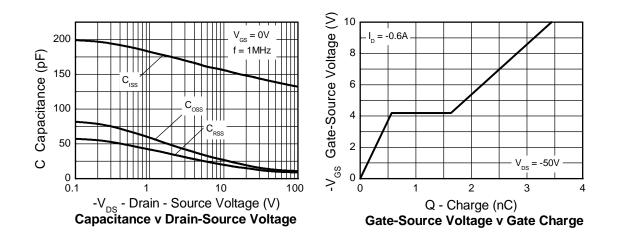


Typical Characteristics

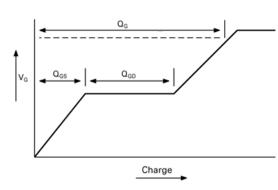




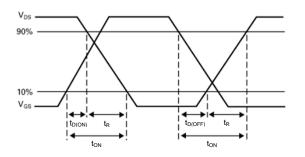
Typical Characteristics (Cont.)



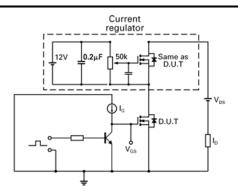
Test Circuits



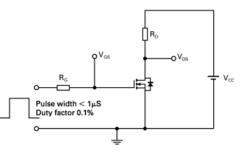
Basic gate charge waveform



Switching time waveforms



Gate charge test circuit



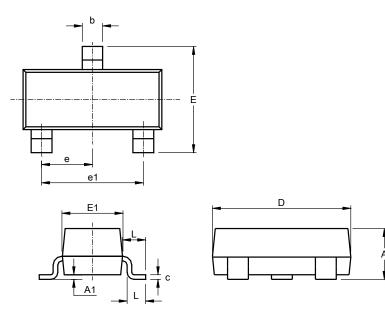




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 (Type DN)

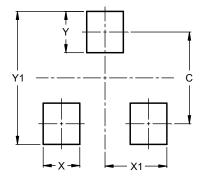


SOT23 (Type DN)					
Dim	Min	Max	Тур		
Α	0.89	1.12	1.00		
A1	0.01	0.10	0.05		
b	0.30	0.51	0.45		
C	0.08	0.20	0.10		
D	2.80	3.04	3.00		
Е	2.10	2.64	2.42		
E1	1.20	1.40	1.37		
е	0.95 REF				
e1	1.90 REF				
L	0.25	0.60	0.30		
L1	0.45	0.62	0.54		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 (Type DN)



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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